

Automotive 750 V, 600 A Dual Side Cooling Half-Bridge Power Module

VE-Trac™ Dual NVG600A75L4DSE2

Product Description

The NVG600A75L4DSE2 is part of VE-Trac™ Dual family of power modules with dual side cooling and compact footprints for Hybrid (HEV) and Electric Vehicle (EV) traction inverter application.

The module consists of two narrow mesa Field Stop (FS4) IGBTs in a half-bridge configuration. The chipset utilizes the new narrow mesa IGBT technology in providing high current density and robust short circuit protection with higher blocking voltage to deliver outstanding performance in EV traction applications.

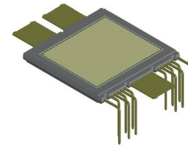
Liquid cooling heatsink reference design, loss models and CAD models are available to support customers in inverter designs.

Features

- Dual-Side Cooling
- Integrated Chip Level Temperature and Current Sensor
- $T_{vj\ max} = 175^{\circ}C$ for Continuous Operation
- Low-Stray Inductance
- Low Conduction and Switching Losses
- Automotive Grade
- 4.2 kV Isolated DBC Substrate
- AEC Qualified and PPAP Capable
- This Device is Pb-Free and is RoHS Compliant

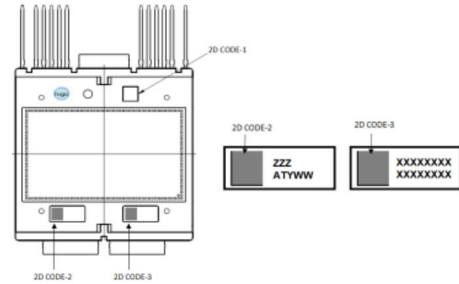
Typical Applications

- Hybrid and Electric Vehicle Traction Inverter
- High Power DC-DC Boost Converter

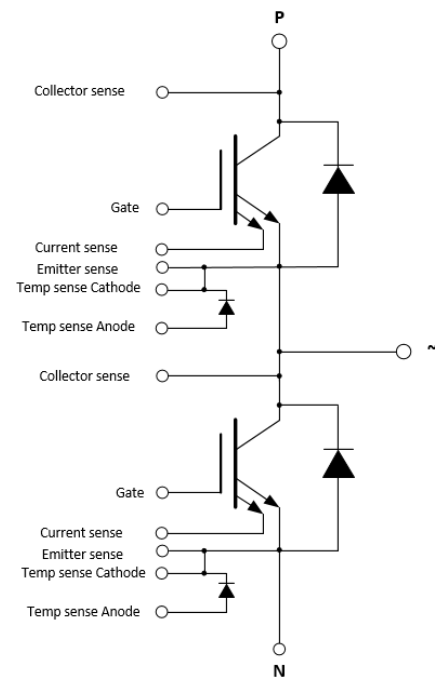


AHPM15-CFA MODULE
 CASE MODHQ

MARKING DIAGRAM



ZZZ = Assembly Lot Code
 AT = Assembly & Test Location
 Y = Year
 WW = Work Week
 XXXX = Specific Device Code



ORDERING INFORMATION

See detailed ordering and shipping information on page 10 of this data sheet.

VE-Trac™ Dual NVG600A75L4DSE2

PIN DESCRIPTION

Pin #	Pin	Pin Function Description	Pin Arrangement
1	N	Low Side Emitter	
2	P	High Side Collector	
3	H/S COLLECTOR SENSE	High Side Collector Sense	
4	H/S CURRENT SENSE	High Side Current Sense	
5	H/S EMITTER SENSE	High Side Emitter Sense	
6	H/S GATE	High Side Gate	
7	H/S TEMP SENSE (CATHODE)	High Side Temp sense Diode Cathode	
8	H/S TEMP SENSE (ANODE)	High Side Temp sense Diode Anode	
9	~	Phase Output	
10	L/S CURRENT SENSE	Low Side Current Sense	
11	L/S EMITTER SENSE	Low Side Emitter Sense	
12	L/S GATE	Low Side Gate	
13	L/S TEMP SENSE (CATHODE)	Low Side Temp sense Diode Cathode	
14	L/S TEMP SENSE (ANODE)	Low Side Temp sense Diode Anode	
15	L/S COLLECTOR SENSE	Low Side Collector Sense	

DBC Substrate

Al₂O₃ isolated substrate, basic isolation, and copper on both sides.

Lead Frame

Copper with Tin electro-plating.

Flammability Information

All materials present in the power module meet UL flammability rating class 94V-0.

MODULE CHARACTERISTICS

Symbol	Parameter	Rating	Unit		
T _{vj}	Continuous Operating Junction Temperature Range	-40 to 175	°C		
T _{STG}	Storage Temperature range	-40 to 125	°C		
V _{ISO}	Isolation Voltage, AC, f = 50 Hz, t = 1 s	4200	V		
CTI	Comparative Tracking Index	>600	-		
		Min	Typ	Max	
Creepage	Pin/Terminal to Pin/Terminal (closest location)	5.0	-	-	mm
Clearance	Pin/Terminal to Pin/Terminal (closest location)	2.9	-	-	mm
L _{sCE}	Stray Inductance	-	8	-	nH
R _{CC'+EE'}	Module Lead Resistance, Terminals - Chip	-	0.15	-	mΩ
G	Module Weight	-	75	-	g

VE-Trac™ Dual NVG600A75L4DSE2

ABSOLUTE MAXIMUM RATINGS (T_{VJ} = 25°C, unless otherwise specified)

Symbol	Parameter	Rating	Unit
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IGBT

V _{CES}	Collector to Emitter Voltage	750	V
V _{GES}	Gate to Emitter Voltage	±20	V
I _{CN}	Implemented Collector Current	600	A
I _{C nom}	Continuous DC Collector Current, T _{vjmax} = 175°C, T _F = 65°C, Ref. Heatsink	500	A
I _{CRM}	Pulsed Collector Current @ V _{GE} = 15 V, t _p = 1 ms	1200	A

DIODE

V _{RRM}	Repetitive Peak Reverse Voltage	750	V
I _{FN}	Implemented Forward Current	600	A
I _F	Continuous Forward Current, T _{vjmax} = 175°C, T _F = 65°C, Ref. Heatsink	400	A
I _{FRM}	Repetitive Peak Forward Current, t _p = 1 ms	1200	A
I ² t value	V _R = 0 V, t _p = 10 ms, T _{VJ} = 150°C T _{VJ} = 175°C	14000 12000	A ² s

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Min	Typ	Max	Unit
IGBT.R _{th,J-C}	Effective R _{th} , Junction to Case	–	0.06	0.08	°C/W
IGBT.R _{th,J-F}	Effective R _{th} , Junction to Fluid, λ _{TIM} = 6 W/m-K, F = 660 N 10 L/min, 65°C, 50/50 EGW, Ref. Heatsink	–	0.146	–	°C/W
Diode.R _{th,J-C}	Effective R _{th} , Junction to Case	–	0.10	0.13	°C/W
Diode.R _{th,J-F}	Effective R _{th} , Junction to Fluid, λ _{TIM} = 6 W/m-K, F = 660 N 10 L/min, 65°C, 50/50 EGW, Ref. Heatsink	–	0.196	–	°C/W

VE-Trac™ Dual NVG600A75L4DSE2

CHARACTERISTICS OF IGBT ($T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified)

Parameters		Conditions	Min	Typ	Max	unit	
V_{CESAT}	Collector to Emitter Saturation Voltage	$V_{GE} = 15\text{ V}, I_C = 400\text{ A},$	$T_{vj} = 25^{\circ}\text{C}$	-	1.23	1.35	V
			$T_{vj} = 150^{\circ}\text{C}$	-	1.28	-	
			$T_{vj} = 175^{\circ}\text{C}$	-	1.30	-	
		$V_{GE} = 15\text{ V}, I_C = 600\text{ A},$	$T_{vj} = 25^{\circ}\text{C}$	-	1.39	-	
			$T_{vj} = 150^{\circ}\text{C}$	-	1.53	-	
			$T_{vj} = 175^{\circ}\text{C}$	-	1.57	-	
I_{CES}	Collector to Emitter Leakage Current	$V_{GE} = 0, V_{CE} = 750\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	-	-	1	mA
			$T_{vj} = 175^{\circ}\text{C}$	-	-	8	
I_{GES}	Gate – Emitter Leakage Current	$V_{CE} = 0, V_{GE} = \pm 20\text{ V}$	-	-	± 400	nA	
V_{th}	Threshold Voltage	$V_{CE} = V_{GE}, I_C = 500\text{ mA}$	4.5	5.6	6.5	V	
Q_G	Total Gate Charge	$V_{GE} = -8\text{ to }15\text{ V}, V_{CE} = 400\text{ V},$ $I_C = 400\text{ A}$	-	1.0	-	μC	
R_{Gint}	Internal Gate Resistance		-	2	-	Ω	
C_{ies}	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	36	-	nF	
C_{oes}	Output Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	0.7	-	nF	
C_{res}	Reverse Transfer Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	0.09	-	nF	
$T_{d.on}$	Turn On Delay, Inductive Load	$I_C = 400\text{ A}, V_{CE} = 400\text{ V}$ $V_{GE} = +15/-8\text{ V}$ $R_{g.on} = 3.9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$	-	194	-	ns
			$T_{vj} = 150^{\circ}\text{C}$	-	224	-	
			$T_{vj} = 175^{\circ}\text{C}$	-	228	-	
T_r	Rise Time, Inductive Load	$I_C = 400\text{ A}, V_{CE} = 400\text{ V}$ $V_{GE} = +15/-8\text{ V}$ $R_{g.on} = 3.9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$	-	71	-	ns
			$T_{vj} = 150^{\circ}\text{C}$	-	89	-	
			$T_{vj} = 175^{\circ}\text{C}$	-	94	-	
$T_{d.off}$	Turn Off Delay, Inductive Load	$I_C = 400\text{ A}, V_{CE} = 400\text{ V}$ $V_{GE} = +15/-8\text{ V}$ $R_{g.off} = 15\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$	-	969	-	ns
			$T_{vj} = 150^{\circ}\text{C}$	-	1047	-	
			$T_{vj} = 175^{\circ}\text{C}$	-	1063	-	
T_f	Fall Time, Inductive Load	$I_C = 400\text{ A}, V_{CE} = 400\text{ V}$ $V_{GE} = +15/-8\text{ V}$ $R_{g.off} = 15\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$	-	123	-	ns
			$T_{vj} = 150^{\circ}\text{C}$	-	202	-	
			$T_{vj} = 175^{\circ}\text{C}$	-	230	-	
E_{ON}	Turn-On Switching Loss (Including Diode Reverse Recovery Loss)	$I_C = 400\text{ A}, V_{CE} = 400\text{ V}$ $V_{GE} = +15/-8\text{ V}$ $R_{g.on} = 3.9\ \Omega$ $L_s = 25\text{ nH}$ $di/dt (T_{vj} = 25^{\circ}\text{C}) = 4.67\text{ A/ns}$ $di/dt (T_{vj} = 175^{\circ}\text{C}) = 3.61\text{ A/ns}$	$T_{vj} = 25^{\circ}\text{C}$	-	10.09	-	mJ
			$T_{vj} = 150^{\circ}\text{C}$	-	16.73	-	
			$T_{vj} = 175^{\circ}\text{C}$	-	18.57	-	
E_{OFF}	Turn-Off Switching Loss	$I_C = 400\text{ A}, V_{CE} = 400\text{ V}$ $V_{GE} = +15/-8\text{ V}$ $R_{g.off} = 15\ \Omega$ $L_s = 25\text{ nH}$ $dv/dt (T_{vj}=25^{\circ}\text{C}) = 2.82\text{ V/ns}$ $dv/dt (T_{vj}=175^{\circ}\text{C}) = 2.08\text{ V/ns}$	$T_{vj} = 25^{\circ}\text{C}$	-	15.95	-	mJ
			$T_{vj} = 150^{\circ}\text{C}$	-	25.06	-	
			$T_{vj} = 175^{\circ}\text{C}$	-	27.30	-	
E_{sc}	Minimum Short Circuit Energy Withstand	$V_{GE} \leq 15\text{ V}, V_{CE} = 400\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	-	3.5	-	J
			$T_{vj} = 175^{\circ}\text{C}$	3.5	-	-	

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CHARACTERISTICS OF INVERSE DIODE ($T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified)

Parameters		Conditions	Min	Typ	Max	unit	
V_F	Diode Forward Voltage	$V_{GE} = 0\text{ V}, I_C = 400\text{ A},$	$T_{vj} = 25^{\circ}\text{C}$	–	1.34	1.47	V
			$T_{vj} = 150^{\circ}\text{C}$	–	1.30	–	
			$T_{vj} = 175^{\circ}\text{C}$	–	1.29	–	
		$V_{GE} = 0\text{ V}, I_C = 600\text{ A},$	$T_{vj} = 25^{\circ}\text{C}$	–	1.48	–	
			$T_{vj} = 150^{\circ}\text{C}$	–	1.47	–	
			$T_{vj} = 175^{\circ}\text{C}$	–	1.46	–	
E_{rr}	Reverse Recovery Energy	$V_R = 400\text{ V}, I_F = 400\text{ A},$ $R_{GON} = 3.9\ \Omega,$ $-di/dt = 3.61\text{ A/ns (175}^{\circ}\text{C)}$ $V_{GE} = -8\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	–	1.05	–	mJ
			$T_{vj} = 150^{\circ}\text{C}$	–	4.93	–	
			$T_{vj} = 175^{\circ}\text{C}$	–	5.90	–	
				–	–	–	
Q_{RR}	Recovered Charge	$V_R = 400\text{ V}, I_F = 400\text{ A},$ $R_{GON} = 3.9\ \Omega,$ $-di/dt = 3.61\text{ A/ns (175}^{\circ}\text{C)}$ $V_{GE} = -8\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	–	11.60	–	μC
			$T_{vj} = 150^{\circ}\text{C}$	–	25.72	–	
			$T_{vj} = 150^{\circ}\text{C}$	–	29.28	–	
				–	–	–	
I_{rr}	Peak Reverse Recovery Current	$V_R = 400\text{ V}, I_F = 400\text{ A},$ $R_{GON} = 3.9\ \Omega,$ $-di/dt = 3.61\text{ A/ns (175}^{\circ}\text{C)}$ $V_{GE} = -8\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	–	241	–	A
			$T_{vj} = 150^{\circ}\text{C}$	–	294	–	
			$T_{vj} = 175^{\circ}\text{C}$	–	304	–	
				–	–	–	

SENSOR CHARACTERISTICS ($T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified)

Parameters		Conditions	Min	Typ	Max	unit	
T_{sense}	Temperature Sense	$I_F = 200\ \mu\text{A},$	$T_{vj} = 25^{\circ}\text{C}$	–	2.159	–	V
			$T_{vj} = 150^{\circ}\text{C}$	–	1.300	–	
			$T_{vj} = 175^{\circ}\text{C}$	–	1.186	–	
I_{sense}	Current Sense	$R_{shunt} = 0.62\ \Omega,$	$I_C = 1200\text{ A}$	–	65	–	mV
			$I_C = 600\text{ A}$	–	39	–	
			$I_C = 100\text{ A}$	–	20	–	

VE-Trac™ Dual NVG600A75L4DSE2

TYPICAL CHARACTERISTICS

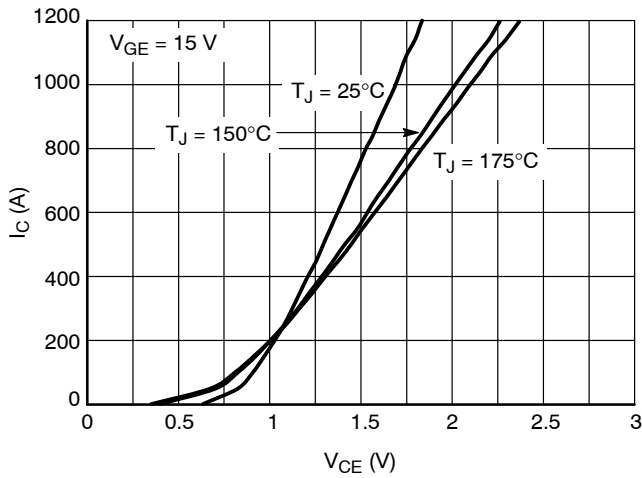


Figure 1. IGBT Output Characteristic

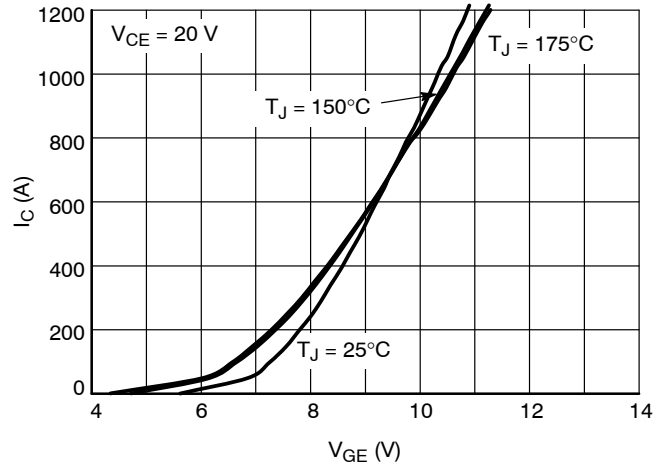


Figure 2. IGBT Transfer Characteristic

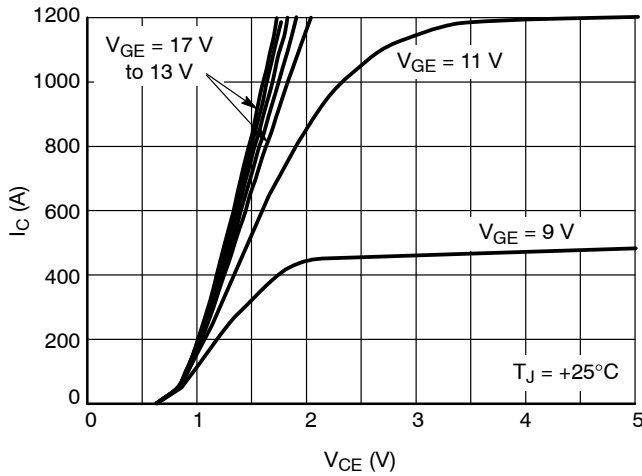


Figure 3. IGBT Output Characteristic, +25°C

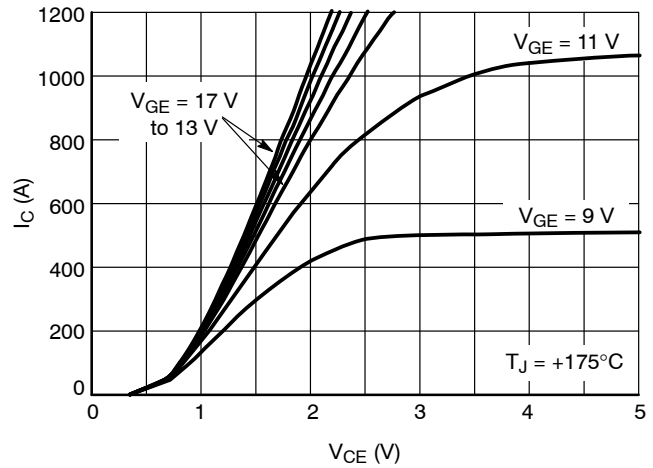


Figure 4. IGBT Output Characteristic, +175°C

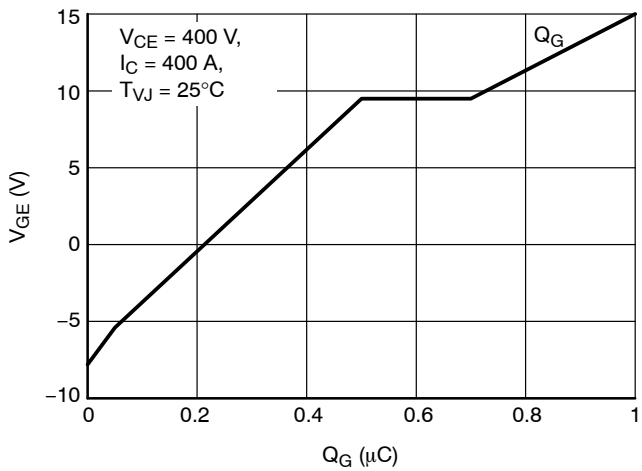


Figure 5. Gate Charge Characteristics

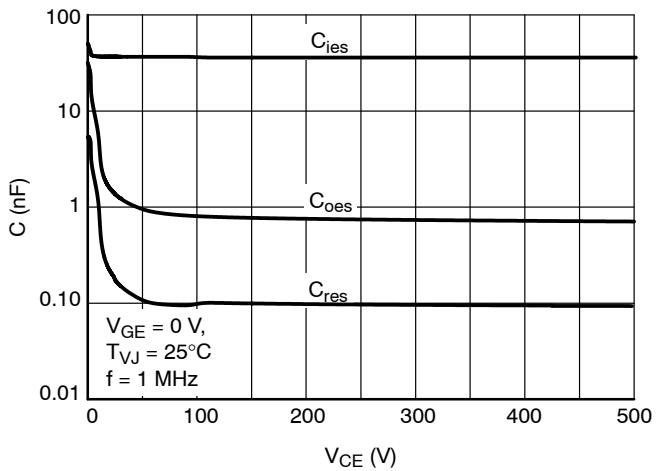


Figure 6. Capacitance Characteristics

VE-Trac™ Dual NVG600A75L4DSE2

TYPICAL CHARACTERISTICS

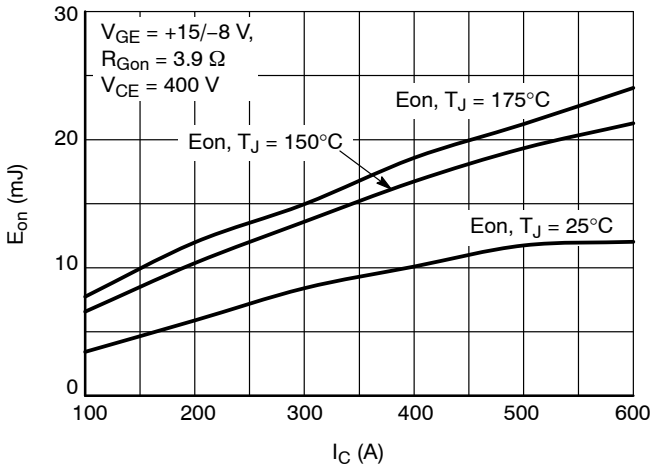


Figure 7. E_{on} vs. I_C

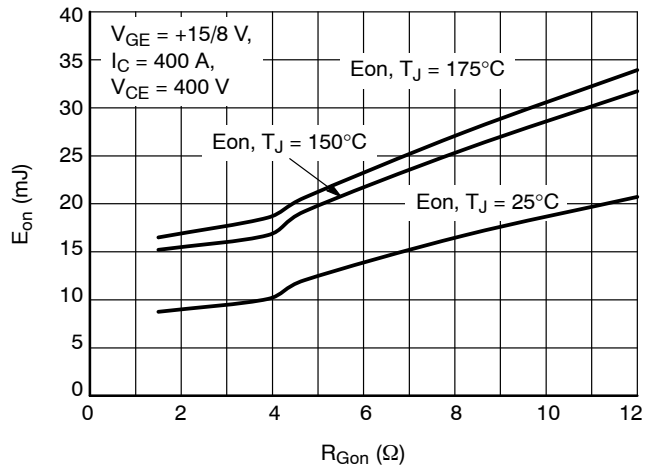


Figure 8. E_{ON} vs. R_{Gon}

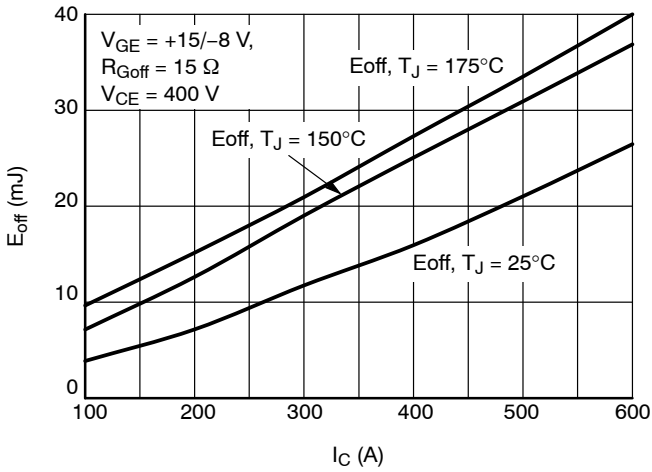


Figure 9. E_{off} vs. I_C

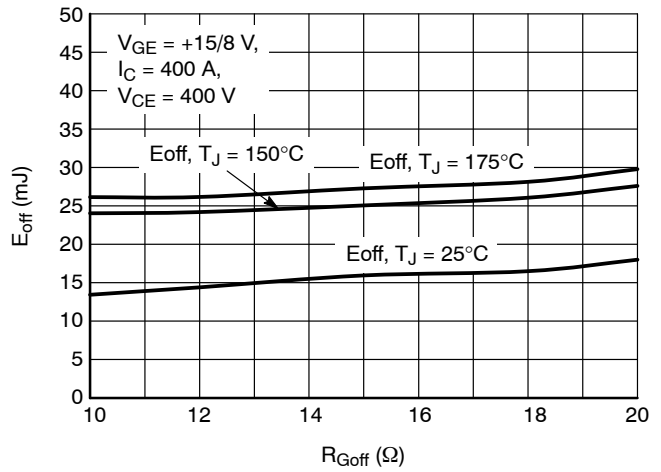


Figure 10. E_{off} vs. R_{Goff}

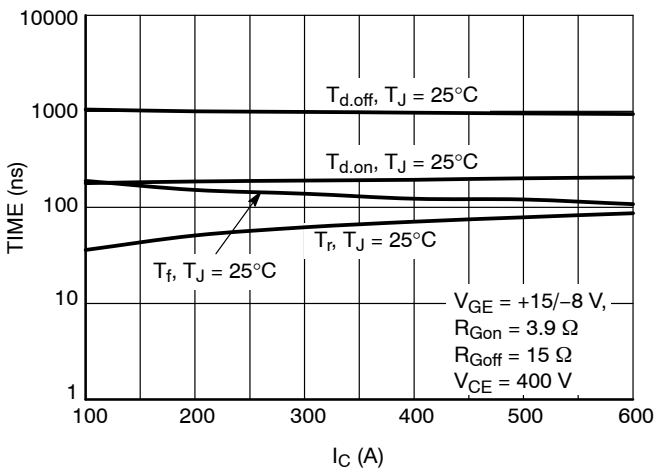


Figure 11. IGBT Switching Times vs. I_C , $T_{vj} = 25^\circ\text{C}$

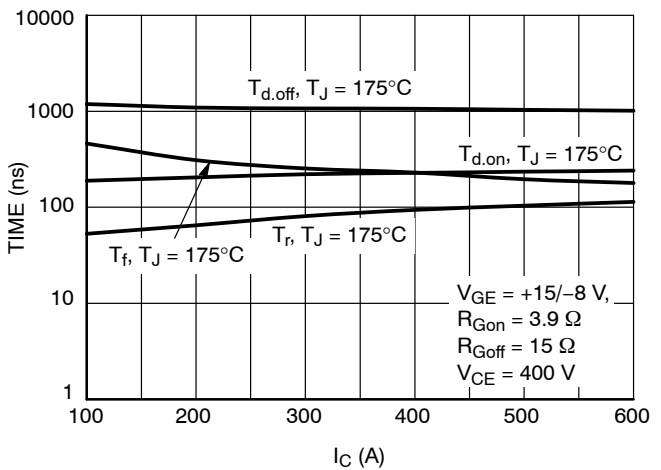


Figure 12. IGBT Switching Times vs. I_C , $T_{vj} = 175^\circ\text{C}$

VE-Trac™ Dual NVG600A75L4DSE2

TYPICAL CHARACTERISTICS

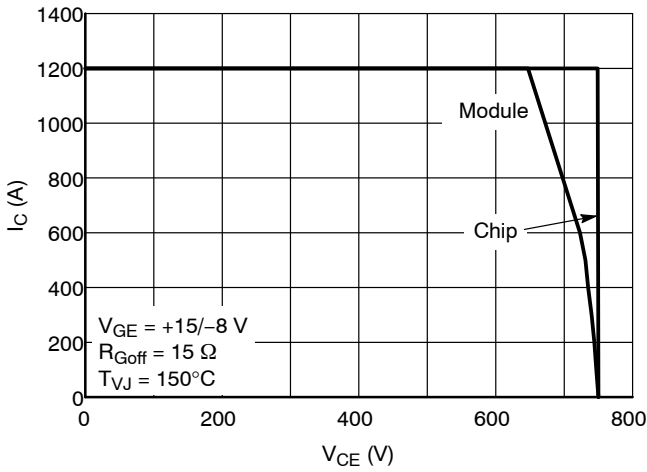


Figure 13. Reverse Bias Safe Operating Area

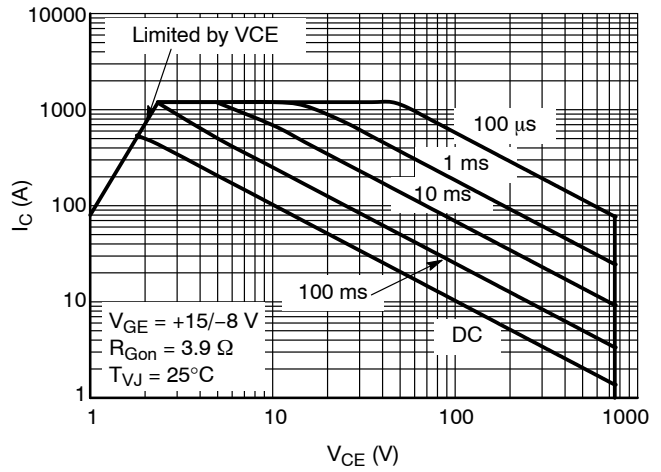


Figure 14. Forward Bias Safe Operating Area

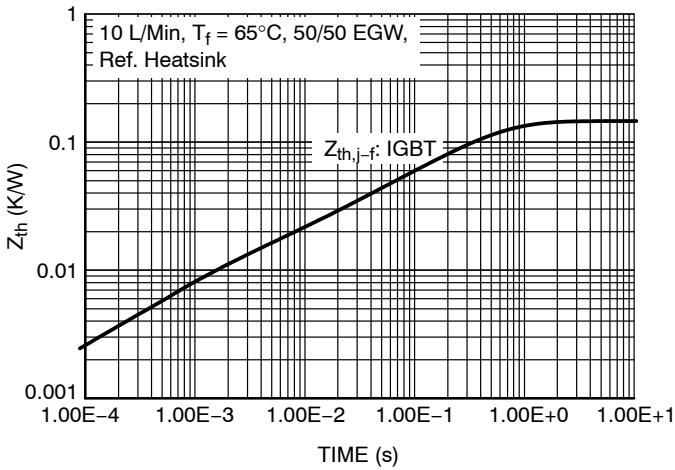


Figure 15. IGBT Transient Thermal Impedance

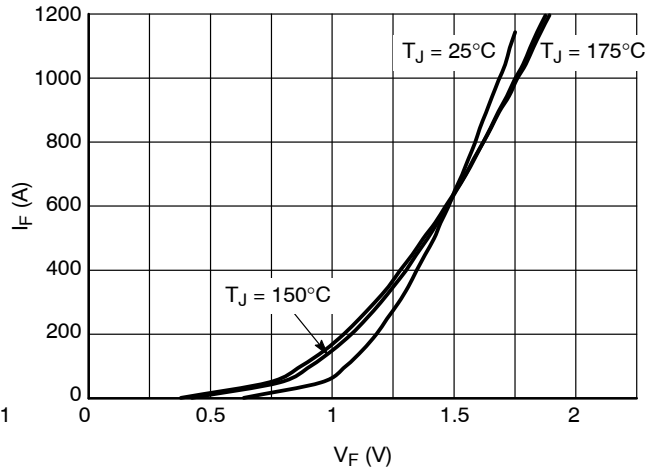


Figure 16. Diode Forward Characteristic

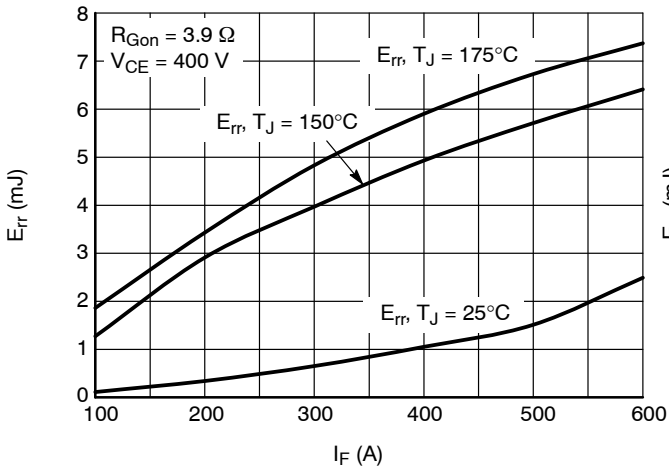


Figure 17. Diode Switching Losses vs. I_F

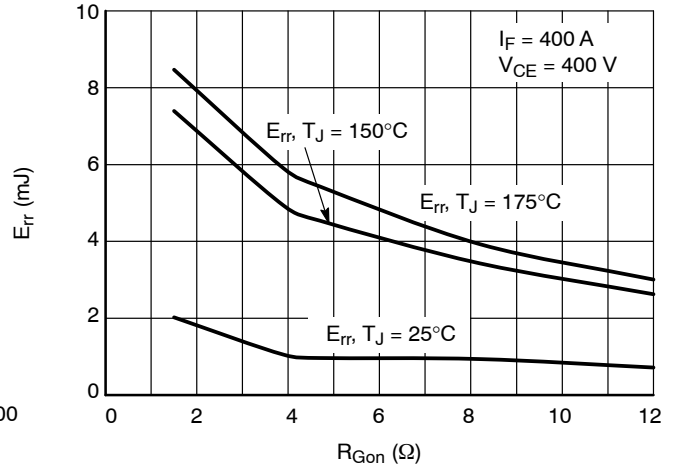


Figure 18. Diode Switching Losses vs. R_{Gon}

TYPICAL CHARACTERISTICS

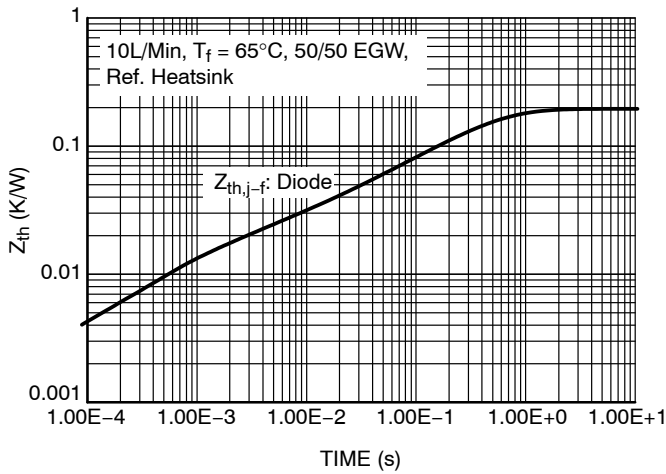


Figure 19. Diode Transient Thermal Impedance

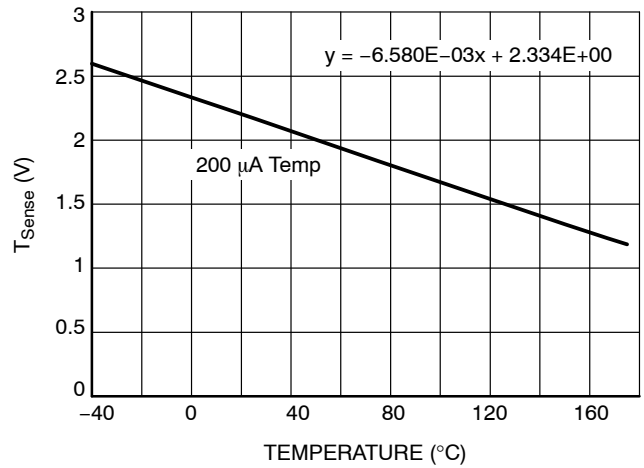


Figure 20. Temperature Sensor Characteristic

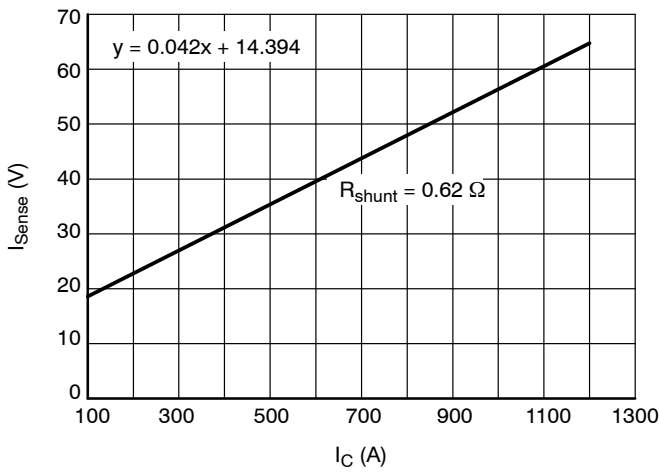


Figure 21. Current Sensor Characteristic

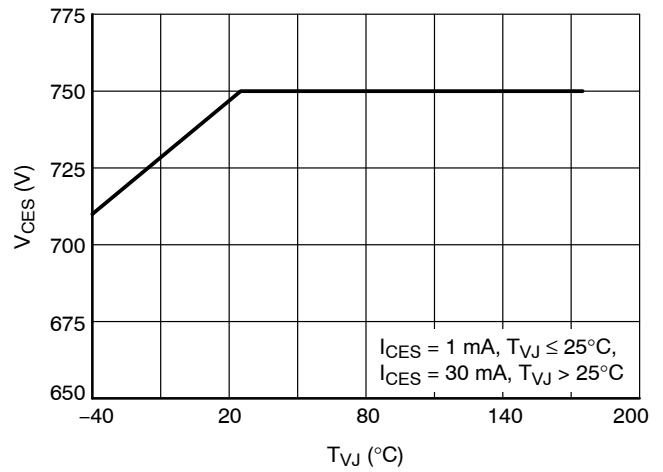


Figure 22. Maximum Allowed V_{CE}

General Note: These are preliminary values measured from a small number of DV units. Values will be updated based on higher quantity of PV measurements.

VE-Trac™ Dual NVG600A75L4DSE2

ORDERING INFORMATION

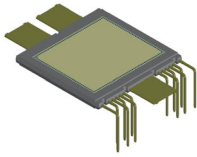
Part Number	Package	Shipping
NVG600A75L4DSE2	AHPM15-CFA Module, Case MODHQ (Pb-Free)	36 Units / 2x Blister Tray

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MECHANICAL CASE OUTLINE

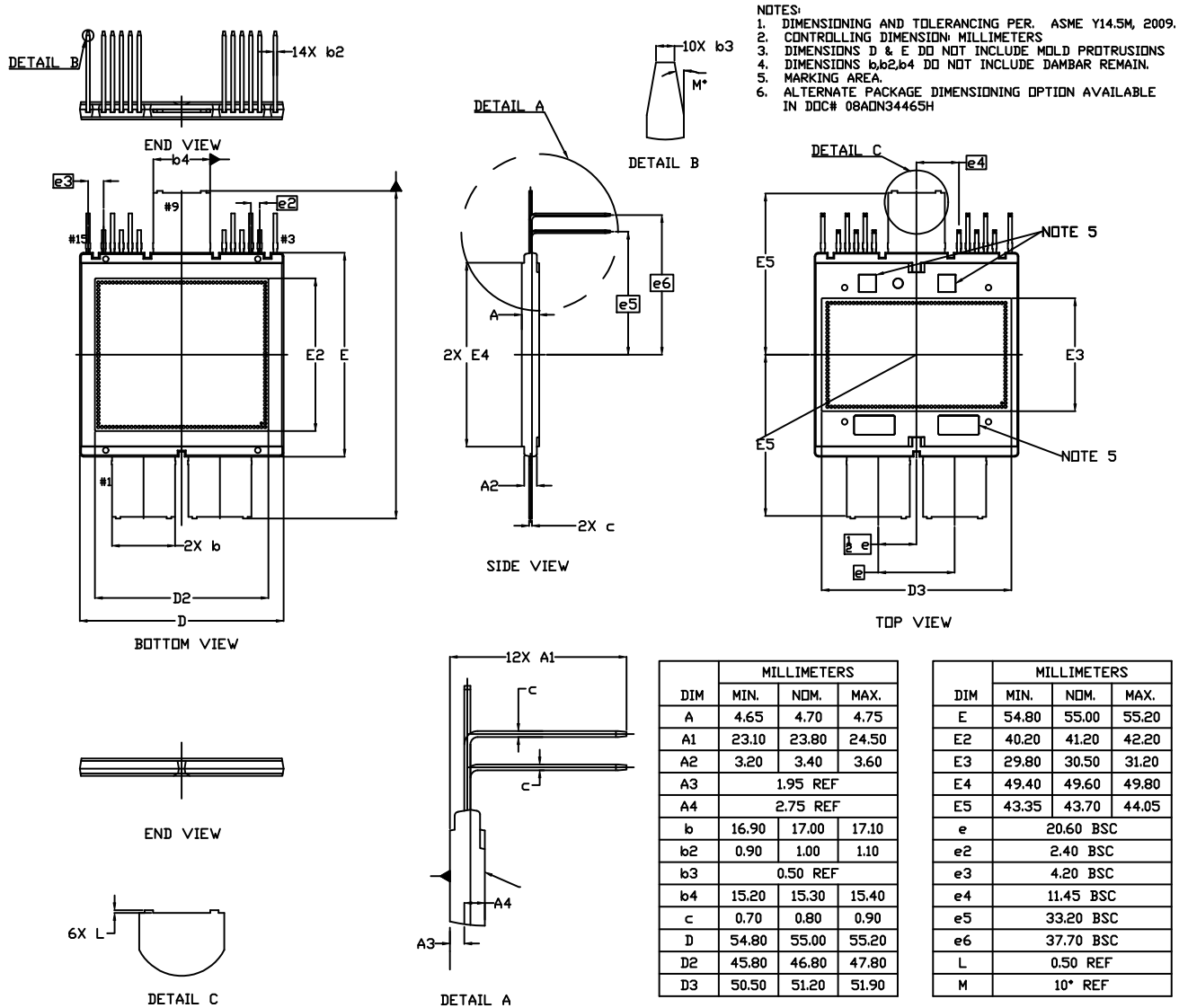
PACKAGE DIMENSIONS

ON Semiconductor®



AHPM15-CFA MODULE CASE MODHQ ISSUE A

DATE 11 JUN 2021



DIM	MILLIMETERS		
	MIN.	NDM.	MAX.
A	4.65	4.70	4.75
A1	23.10	23.80	24.50
A2	3.20	3.40	3.60
A3	1.95 REF		
A4	2.75 REF		
b	16.90	17.00	17.10
b2	0.90	1.00	1.10
b3	0.50 REF		
b4	15.20	15.30	15.40
c	0.70	0.80	0.90
D	54.80	55.00	55.20
D2	45.80	46.80	47.80
D3	50.50	51.20	51.90

DIM	MILLIMETERS		
	MIN.	NDM.	MAX.
E	54.80	55.00	55.20
E2	40.20	41.20	42.20
E3	29.80	30.50	31.20
E4	49.40	49.60	49.80
E5	43.35	43.70	44.05
e	20.60 BSC		
e2	2.40 BSC		
e3	4.20 BSC		
e4	11.45 BSC		
e5	33.20 BSC		
e6	37.70 BSC		
L	0.50 REF		
M	10° REF		

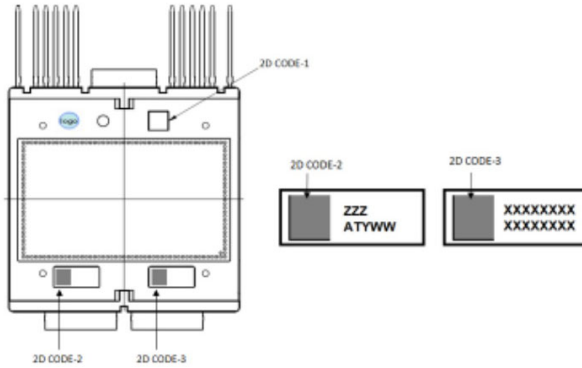
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DESCRIPTION:	AHPM15-CFA MODULE	PAGE 1 OF 2

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**AHPM15-CFA MODULE
CASE MODHQ
ISSUE A**

DATE 11 JUN 2021


**GENERIC
MARKING DIAGRAM***



ZZZ = Assembly Lot Code
 AT = Assembly & Test Location
 Y = Year
 WW = Work Week
 XXXX = Specific Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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